

isc N-Channel MOSFET Transistor

2SK600

DESCRIPTION

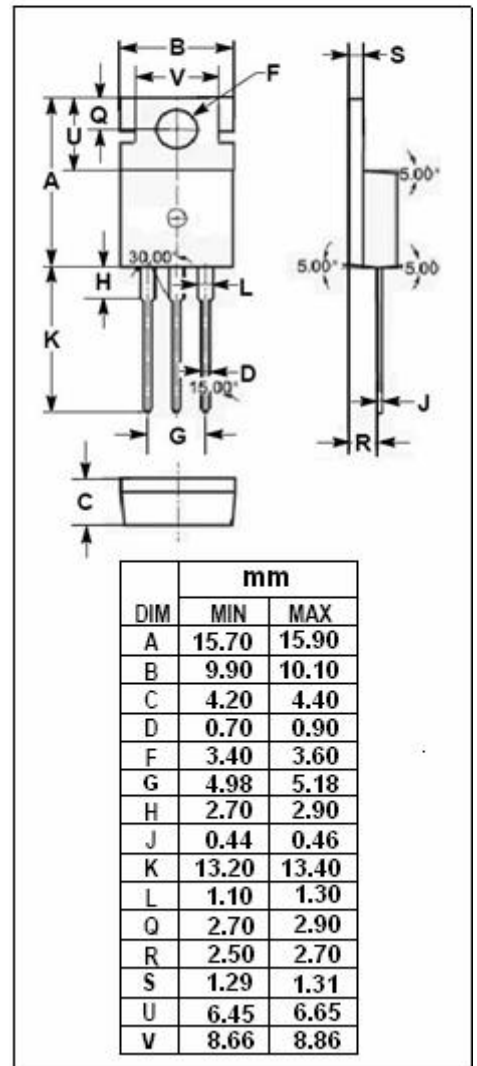
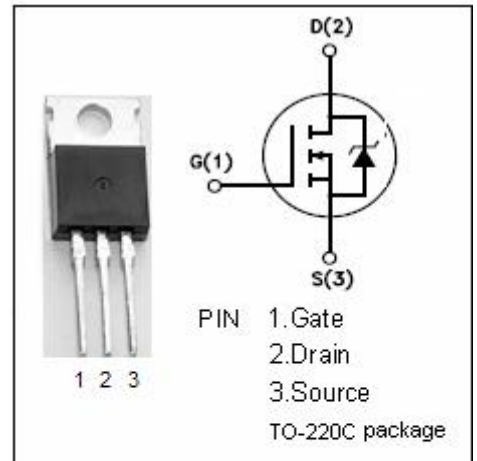
- Drain Current $-I_D = 25A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 60V (Min)$
- Fast Switching Speed

APPLICATIONS

- High speed power switching

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	ARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage ($V_{GS} = 0$)	60	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-continuous@ $TC = 25^\circ C$	25	A
P_{tot}	Total Dissipation@ $TC = 25^\circ C$	75	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



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• ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=1\text{mA}$	60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=1\text{mA}$	2.0		4.0	V
$R_{DS(on)}$	Drain-Source On-stage Resistance	$V_{GS}=10\text{V}; I_D=15\text{A}$			0.055	Ω
I_{GSS}	Gate Source Leakage Current	$V_{GS}= \pm 20\text{V}; V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=50\text{V}; V_{GS}=0$			1	μA
V_{SD}	Diode Forward Voltage	$I_F=25\text{A}; V_{GS}=0$		1.3	1.7	V
t_r	Rise time	$V_{GS}=10\text{V}; I_D=3\text{A};$ $R_L=50\ \Omega$		50	75	ns
t_{on}	Turn-on time			75	115	ns
t_f	Fall time			80	110	ns
t_{off}	Turn-off time			240	330	ns